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IN THE CLAIMS

Please amend the claims as set forth herein.

Claims 1-7 (Canceled).

8. (Currently Amended) A method of producing a semiconductor wafer, comprising the steps of:

producing a single crystalline semiconductor ingot with a large vacancy-rich region by removing an OiSF ring by means of moving the OiSF ring from a center of a single crystalline semiconductor growth axis to a circumference and by extending a first area and a second area constituting part of said large vacancy-rich region in which it is easy to produce bulk micro-defects of high density and in which delta (Oi), as an oxygen concentration difference between initial oxygen concentration and oxygen concentration after heat treatment in N₂ ambience at 1000 °C for 64 hours, is increased more than other areas, said first and second areas covering all of the wafer except the circumference;

providing a wafer by slicing the single crystalline semiconductor ingot;

carrying out a heat treatment on the wafer at a temperature equal to or higher than 1200 °C under a non-oxidative atmosphere containing hydrogen; and

carrying out a rapid thermal annealing on the wafer at a temperature equal to or lower than 800°C for a period having a duration of two minutes or less.